

MITSUBISHI TRANSISTOR MODULES

QM100DY-HBKHIGH POWER SWITCHING USE
INSULATED TYPE**QM100DY-HBK**

- **IC** Collector current **100A**
- **V_{CEX}** Collector-emitter voltage **600V**
- **h_{FE}** DC current gain **750**
- **Insulated Type**
- **UL Recognized**

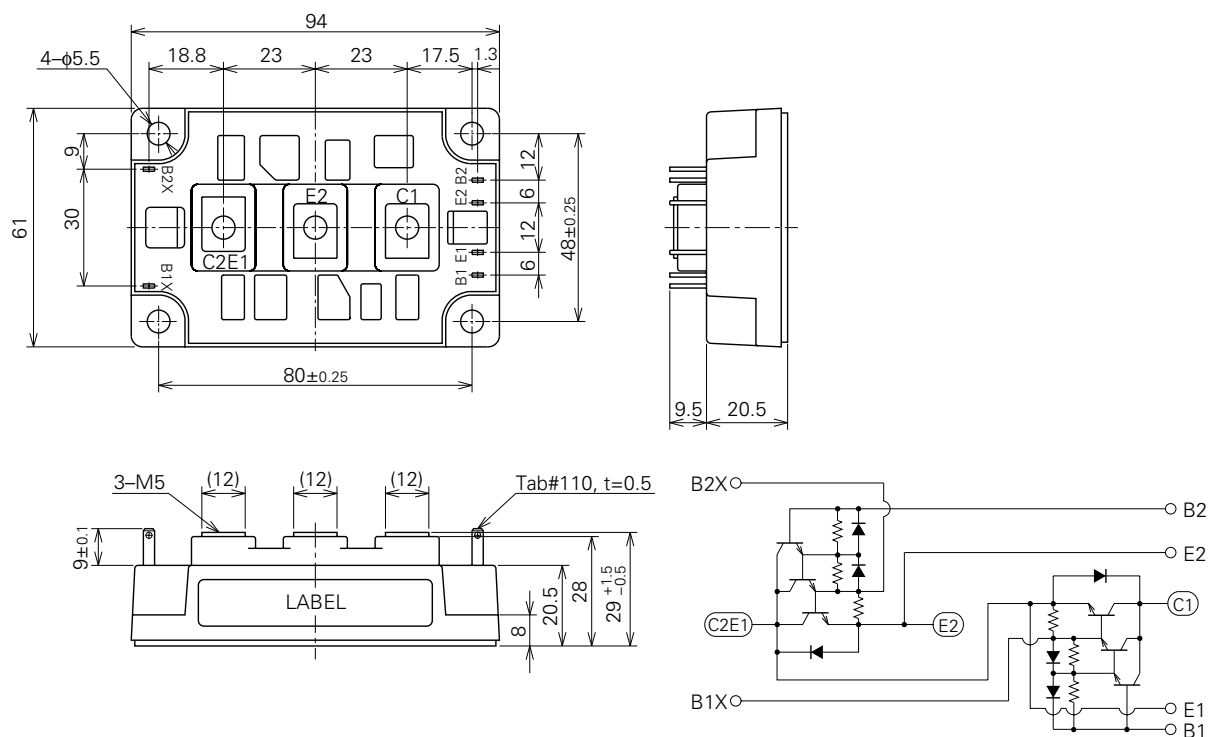
Yellow Card No. E80276 (N)
File No. E80271

APPLICATION

Inverters, Servo drives, DC motor controllers, NC equipment, Welders

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Feb.1999



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ABSOLUTE MAXIMUM RATINGS (Tj=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VCEX (SUS)	Collector-emitter voltage	IC=1A, VEB=2V	600	V
VCEX	Collector-emitter voltage	VEB=2V	600	V
VCBO	Collector-base voltage	Emitter open	600	V
VEBO	Emitter-base voltage	Collector open	7	V
IC	Collector current	DC	100	A
−IC	Collector reverse current	DC (forward diode current)	100	A
PC	Collector dissipation	Tc=25°C	620	W
IB	Base current	DC	6	A
−ICSM	Surge collector reverse current (forward diode current)	Peak value of one cycle of 60Hz (half wave)	1000	A
Tj	Junction temperature		−40~+150	°C
Tstg	Storage temperature		−40~+125	°C
Viso	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Main terminal screw M5	1.47~1.96	N·m
			15~20	kg·cm
		Mounting screw M5	1.47~1.96	N·m
			15~20	kg·cm
—	Weight	Typical value	420	g

ELECTRICAL CHARACTERISTICS (Tj=25°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICEX	Collector cutoff current	VCE=600V, VEB=2V	—	—	2.0	mA
ICBO	Collector cutoff current	VCB=600V, Emitter open	—	—	2.0	mA
IEBO	Emitter cutoff current	VEB=7V	—	—	100	mA
VCE (sat)	Collector-emitter saturation voltage	IC=100A, IB=0.13A	—	—	2.5	V
VBE (sat)	Base-emitter saturation voltage		—	—	3.0	V
−VCEO	Collector-emitter reverse voltage	−IC=100A (diode forward voltage)	—	—	1.8	V
hFE	DC current gain	IC=100A, VCE=2.5V	750	—	—	—
ton	Switching time	VCC=300V, IC=100A, IB1=0.2A, −IB2=2.0A	—	—	2.5	μs
ts			—	—	10	μs
tf			—	—	2.0	μs
Rth (j-c) Q	Thermal resistance (junction to case)	Transistor part (per 1/2 module)	—	—	0.2	°C/W
Rth (j-c) R		Diode part (per 1/2 module)	—	—	0.65	°C/W
Rth (c-f)	Contact thermal resistance (case to fin)	Conductive grease applied (per 1/2 module)	—	—	0.1	°C/W

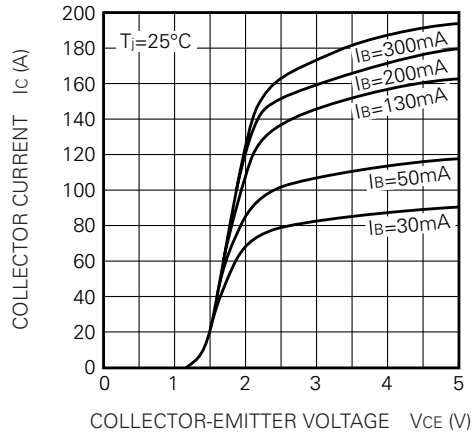
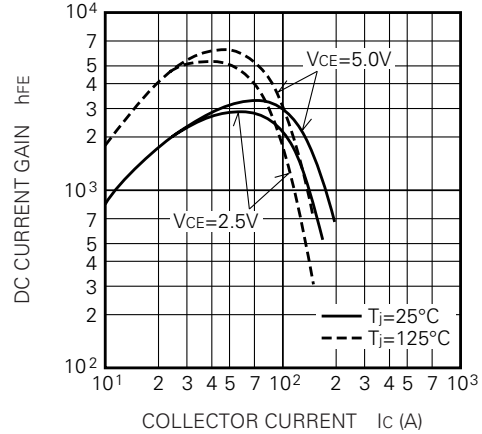
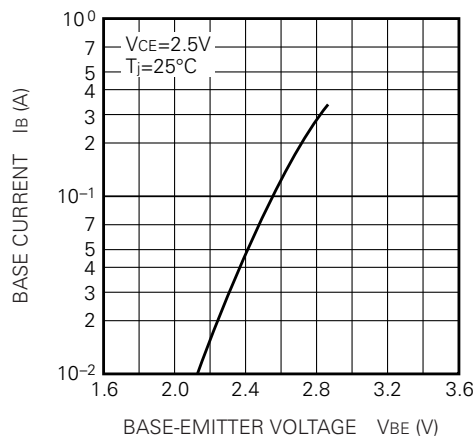
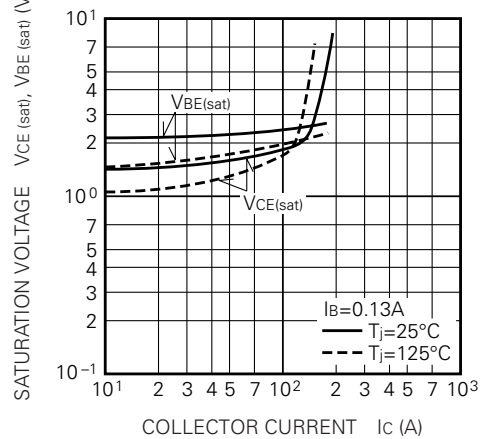
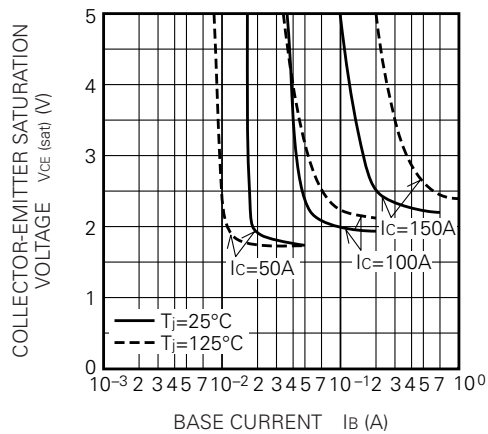
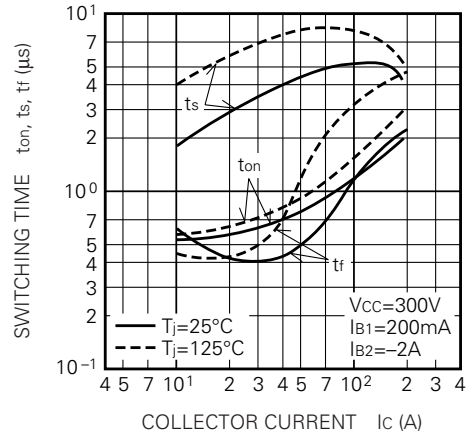


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PERFORMANCE CURVES

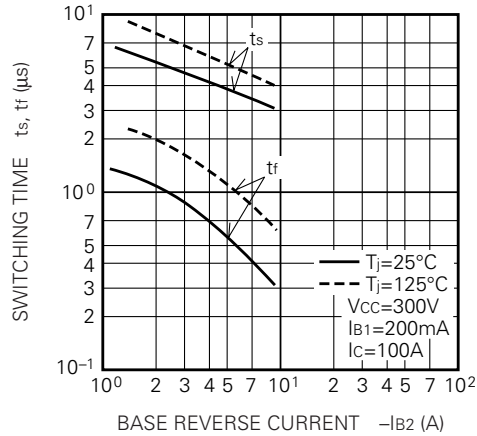
COMMON EMITTER OUTPUT
CHARACTERISTICS (TYPICAL)DC CURRENT GAIN VS.
COLLECTOR CURRENT (TYPICAL)COMMON EMITTER INPUT
CHARACTERISTIC (TYPICAL)SATURATION VOLTAGE
CHARACTERISTICS (TYPICAL)COLLECTOR-EMITTER SATURATION
VOLTAGE (TYPICAL)SWITCHING TIME VS. COLLECTOR
CURRENT (TYPICAL)

Feb.1999

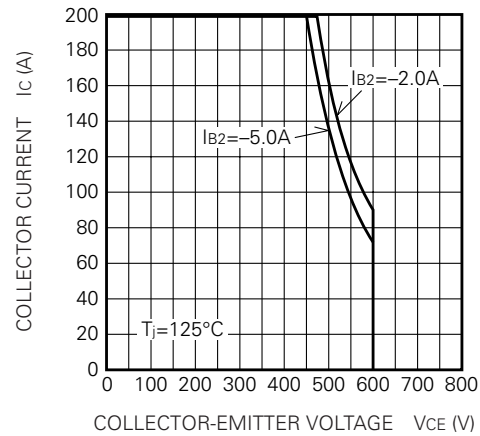


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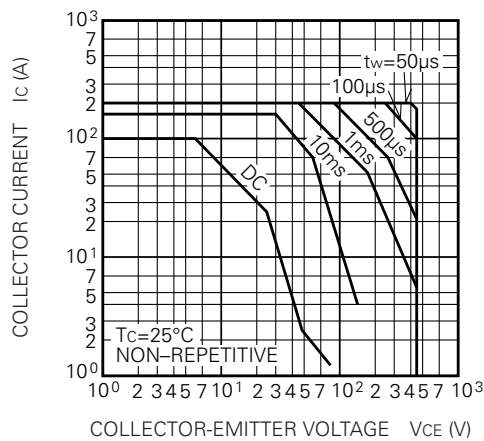
QM100DY-HBK

HIGH POWER SWITCHING USE
INSULATED TYPESWITCHING TIME VS. BASE
CURRENT (TYPICAL)

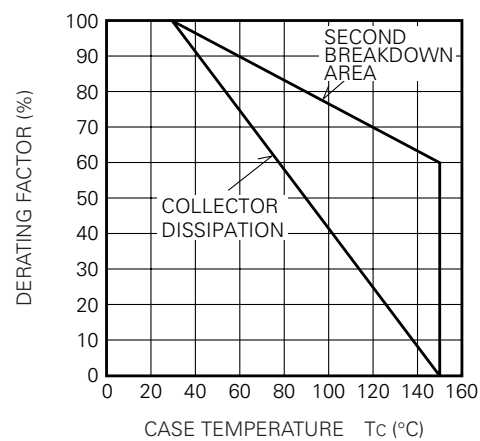
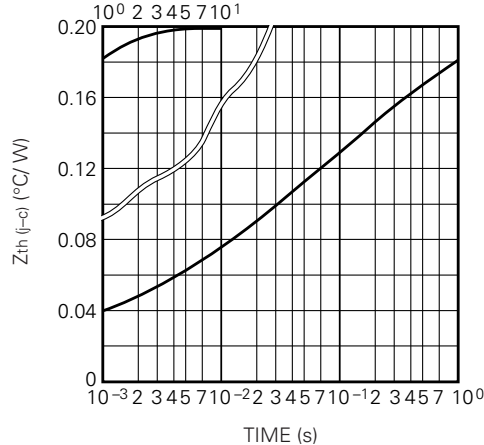
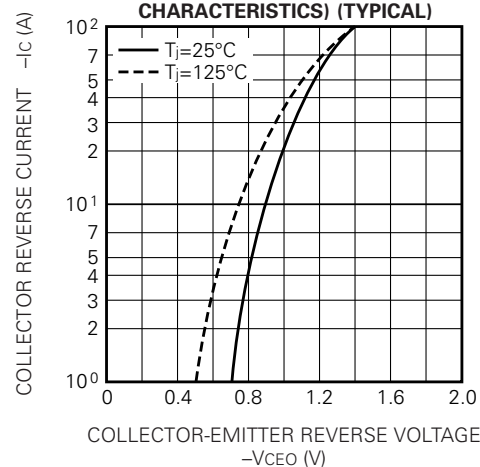
REVERSE BIAS SAFE OPERATING AREA



FORWARD BIAS SAFE OPERATING AREA



DERATING FACTOR OF F. B. S. O. A.

TRANSIENT THERMAL IMPEDANCE
CHARACTERISTIC (TRANSISTOR)REVERSE COLLECTOR CURRENT VS.
COLLECTOR-EMITTER REVERSE
VOLTAGE (DIODE FORWARD
CHARACTERISTICS) (TYPICAL)

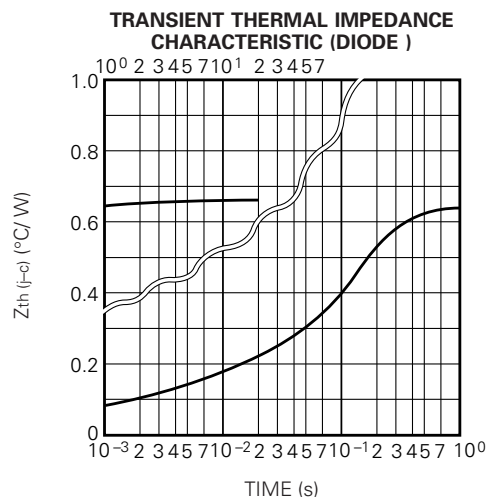
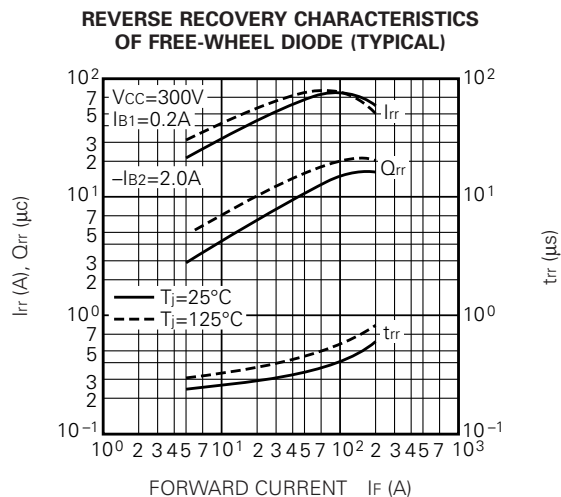
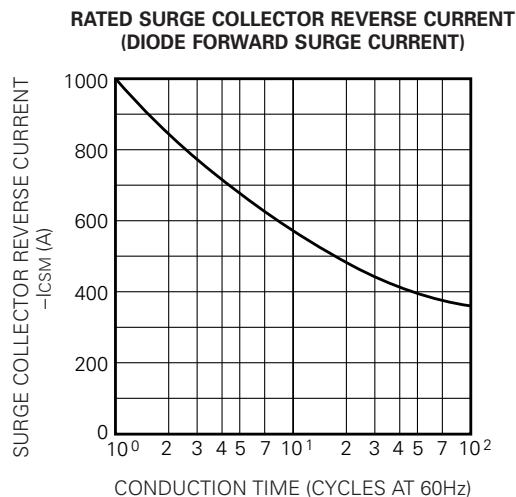
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